

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Koichiro INOMATA, et al.

SERIAL NO: NEW APPLICATION

FILED: HEREWITH

FOR: MAGNETORESISTIVE ELEMENT AND MAGNETIC MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were cited in prior application Serial No. 10/443,830, where required, as were either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 250340US0SRD DIV		SERIAL NO. NEW APPLICATION	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Koichiro INOMATA, et al.			
				FILING DATE HEREWITH		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,287,238	02/15/1994	P. M. Baumgart et al.			
	AB	5,578,385	11/1996	Saito et al.			
	AC	5,534,355	07/1996	Ukono et al.			
	AD	5,747,859	05/1998	Mizushima et al.			
	AE	5,616,370	04/1997	Ukono et al.			
	AF	5,700,588	12/1997	Saito et al.			
	AG	5,773,156	06/1998	Inomata et al.			
	AH	6,069,820	05/2000	Inomata et al.			
	AI	5,500,633	03/1996	Saito et al.			
	AJ	5,716,719	02/1998	Saito et al.			
	AK	5,523,172	06/1996	Saito et al.			
	AL	5,365,212	11/1994	Saito et al.			
	AM	5,973,334	10/1999	Mizushima et al.			
	AN	5,304,975	04/1994	Saito et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	11-177161	07/02/1999	Japan			
	AP	JP 11238924 A	08/1999	Japan			
	AQ	9-260743	10/1997	Japan			
	AR	10-4227	01/1998	Japan			
	AS	11-163436	06/1999	Japan (w/English Abstract)			
	AT	1999-0036653	05/1999	Korea			
	AU	3004005	01/2000	Japan (w/English Abstract)			
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	F. MONTAIGNE et al., Applied Physics Letters, vol. 73, no. 19, pp. 2829-2831, "Enhanced Tunnel Magnetoresistance at High Bias Voltage in Double-Barrier Planar Junctions," 11/9/1998					
	AX	J.C. SLONCZEWSKI, Journal of Magnetism and Magnetic Materials, vol. 159, pp. L1-L7, "Current-Driven Excitation of Magnetic Multilayers," 1996					
	AY	J.Z. SUN, Journal of Magnetism and Magnetic Materials, vol. 202, pp. 157-162, "Current-Driven Magnetic Switching in Manganite Trilayer Junctions," 1999					
	AZ	J. S. MOODERA et al., Physical Review Letters, vol. 74, no. 16, pp. 3273-3276, "Large Magnetoresistance at Room Temperature in Ferromagnetic Thin Film Tunnel Junctions," 4/17/1995				<input checked="" type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,953,248	09/1999	Chen et al.			
	AB	5,636,093	06/1997	Gijs et al.			
	AC	5,757,056	05/1998	Chui			
	AD	6,178,074	01/2001	Gill			
	AE	6,259,586	07/2001	Gill			
	AF	6,275,363	08/2001	Gill			
	AG	5,969,978	10/1999	Prinz			
	AH	6,097,626	08/2000	Brug			
	AI	6,556,473	04/29/2003	Saito et al.			
	AJ	6,381,171	04/30/2002	Inomata et al.			
	AK	6,473,336	10/29/2002	Nakajima et al.			
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Xiangdong ZHANG et al., Physical Review B, vol. 56, no. 9, pp. 5484-5488, "Spin-Polarized Tunneling and Magnetoresistance in Ferromagnet/Insulator (Semiconductor) Single and Double Tunnel Junctions Subjected to an Electric Field," 9/1/1997					
	AX	L.F. SCHLEP et al., Physical Review B., vol. 56, no. 10, pp. R5747-R5750, "Spin-Dependent Tunneling with Coulomb Blockage," 9/1/1997.					
	AY	Jagdeesh S. MOODERA et al., J. Appl. Phys., vol. 79, no. 8, pp. 4724-4729, "Ferromagnetic-Insulator-Ferromagnetic Tunneling: Spin-Dependent Tunneling and Large Magnetoresistance in Trilayer Junctions (invited)," 4/15/1996					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
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